Single Event Upsets in the PANDA EMC

Results from neutron and proton irradiations of the digitiser board



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Front-end electronics in the Electromagnetic Calorimeter

 \sim 600 front-end digitiser boards in the EMC

375 in Barrel 225 in Forward Endcap

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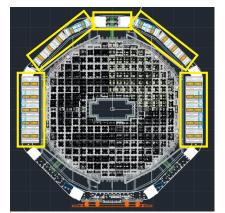


Figure courtesy of C. Schnier.

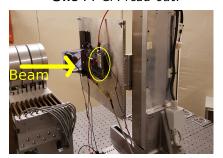
- Distributed over several crates placed around the detector perimeter.
- Two Xilinx Kintex-7 FPGAs per board.
- Of interest here: SEUs caused by neutrons and protons in FPGA.
- Interesting also for other subdetectors.

Proton irradiation

▶ In November 2016 at the AGOR cyclotron at KVI.

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- Board perpendicular to the beam (covering half of the board).
 One FPGA read out.



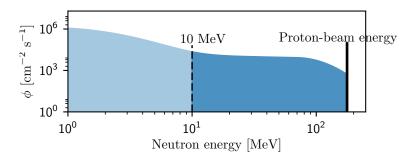
- Three proton energies:
 - ▶ 184 MeV (primary beam energy)
 - ▶ 80 and 100 MeV (with degrader)
- ► Total proton fluence:
 - $\sim 4 \cdot 10^9 \text{ cm}^{-2}$.

High-energy neutron irradiation

- ▶ In June 2016 at the The Svedberg Laboratory (TSL) in Uppsala.
- ▶ Proton beam (180 MeV) \rightarrow W target \rightarrow Neutron beam. Board perpendicular to the beam. **One** FPGA read out.

High-energy neutron irradiation

- ▶ In June 2016 at the The Svedberg Laboratory (TSL) in Uppsala.
- ▶ Proton beam (180 MeV) \rightarrow W target \rightarrow Neutron beam. Board perpendicular to the beam. **One** FPGA read out.
- ► Total neutron fluence: $2 \cdot 10^9$ cm⁻² (>10 MeV).

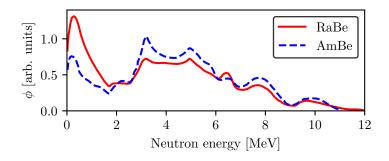


Low-energy neutron irradiation

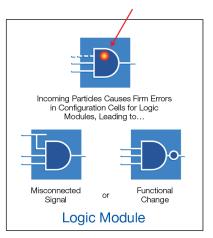
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- Separate measurements using RaBe and AmBe neutron sources. One FPGA read out.

Low-energy neutron irradiation

- ▶ In December 2017 January 2018 at Stockholm University.
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- ▶ Total neutron fluence: $1 \cdot 10^{10}$ cm⁻².

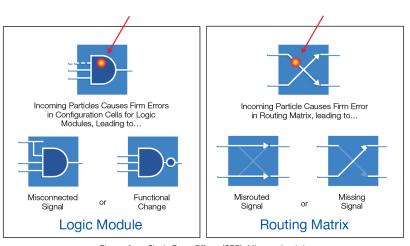


Single Event Upsets (SEUs) in FPGAs



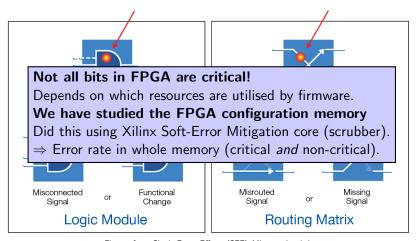
Figures from Single Event Effects (SEE), Microsemi website.

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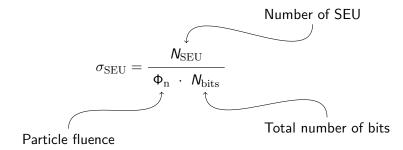
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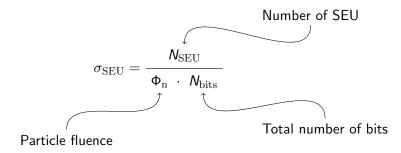
SEU cross section

The cross section (per bit) for an SEU in the FPGA is given by



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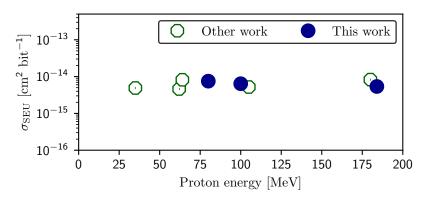
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Once the cross section and particle flux are known, the *SEU rate* and *mean time between upsets* may be determined.

Proton irradiation

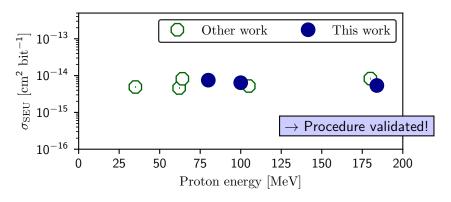
Good agreement with other measurements on Kintex-7:



Other work from for example ATLAS (LAr) and LHCb (RICH) groups.

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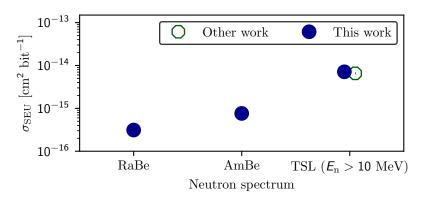
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Neutron irradiations

Good agreement with other measurement on Kintex-7:



Other work from ATLAS (LAr) group.
TSL cross section determined from neutron fluence above 10 MeV.

What does this mean for PANDA?

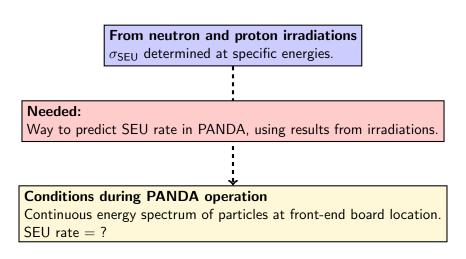
From neutron and proton irradiations $\sigma_{\rm SEU}$ determined at specific energies.

Conditions during PANDA operation

Continuous energy spectrum of particles at front-end board location.

SEU rate = ?

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From neutron and proton irradiations $\sigma_{\rm SEU}$ determined at specific energies.

Solution: Monte Carlo simulations

- 1) Geant4-based model of energy deposits in microelectronics $\Rightarrow \sigma_{\mathsf{SEU}}(E)$
- 2) pandaROOT simulation $\Rightarrow \Phi(E)$

Conditions during PANDA operation

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Developing the SEU model

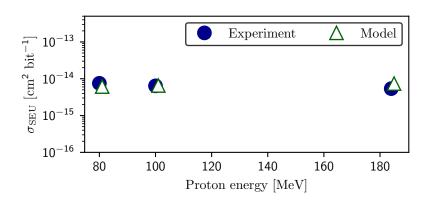
- Model of energy deposition by protons and neutrons in a memory cell.
- Principle based on standard SEU-modelling tools constructed to match Kintex-7 feature size.
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- Model of energy deposition by protons and neutrons in a memory cell.
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- In the model, an SEU occurs if the energy deposition in the sensitive volume is larger than a critical energy.
- ► The values of the model parameters were determined by fitting the model to our experimental data:
 - Simulate proton and neutron beams matching experiments.
 - Fit to all our data using a full likelihood fit.
- When this was done, the model was verified by comparing the resulting cross sections with the experimental data.

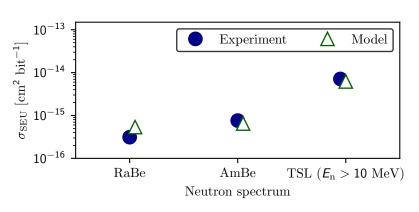
SEU model verification





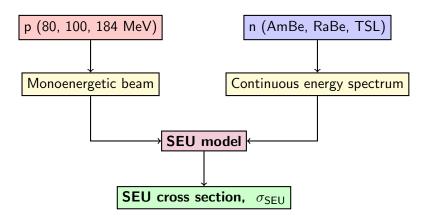
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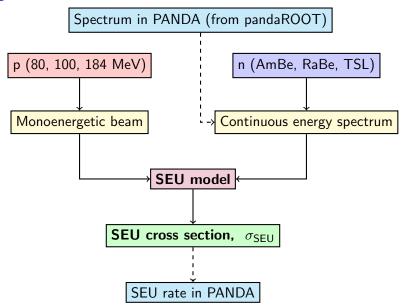


Model works for both protons and neutrons.

Using the SEU model



Using the SEU model



- ▶ Simulations performed at antiproton momenta of 1.5, 5.2 and 8.9 GeV/c (to cover the entire phase-1 range) → neutron flux at **forward endcap** digitisers.
- ▶ All three resulting spectra used as input to the SEU model \rightarrow SEU rates (assuming $\mathcal{L}=1\cdot 10^{31}~\text{cm}^{-2}~\text{s}^{-1}$).

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 - ϕ_n at position of digitisers is $\sim 300 \text{ cm}^{-2} \text{ s}^{-1}$.
 - MTBU due to neutrons (per FPGA):
 - Any type of SEU: 18 hours.
 - ▶ SEUs not correctable by SEM: 180 hours (\sim 10% of all errors).

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- ► These values include a safety factor of 10 relative to the results predicted by the model.

Outlook: Error-mitigation?

- At PANDA startup, triple modular redundancy is probably not necessary when it comes to the FPGA configuration.
- ▶ Xilinx SEM protects the configuration (by scrubbing), and can be used in *enhanced* mode repairs some multi-bit upsets as well \rightarrow decreases uncorrectable-error rate from $\sim \! \! 10\% \rightarrow \! \! \! \sim \! \! 2\%$ (takes up more resources). Full protection: store copy of bitstream which can replace damaged one.

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- Protection for other parts of the FPGA (like Block Memory) has to be incorporated in design.
- ▶ At higher luminosities, TMR might be needed.
- In any case, watch-dog mechanisms have to be included in FPGA design.
- ▶ All this should be taken into account when designing the final firmware (mitigation approach depends on which resources are used). ⇒ Topic for further discussion.

Thank you!

Extra slide: σ_{SEU} energy dependence

